

## FNK N-Channel Enhancement Mode Power MOSFET

### Description

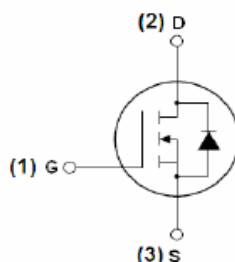
The FNK10N02-A uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. It can be used in a wide variety of applications.

### General Features

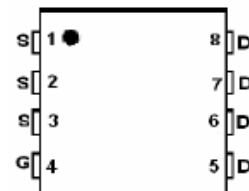
- $V_{DS} = 20V, I_D = 180A$   
 $R_{DS(ON)} < 2.25m\Omega$  @  $V_{GS} = 10V$
- High density cell design for ultra low  $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- Good stability and uniformity with high EAS
- Special process technology for high ESD capability

### Application

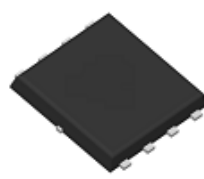
- Load switching
- Power switching application
- Uninterruptible power supply



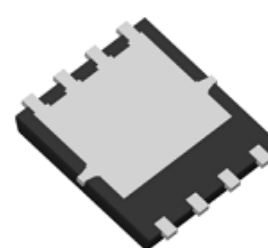
Schematic diagram



Marking and pin Assignment



Top View



Bottom View

### PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK10N02	FNK10N02-A	DFN5X6-8L	-	-	-

### ABSOLUTE MAXIMUM RATINGS( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D(25^\circ C)$	180	A
	$I_{DM}$	720	A
Maximum Power Dissipation	$P_D$	83	W
Single pulse avalanche energy(Note 5)	EAS	504	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	1.5	$^\circ C/W$
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### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
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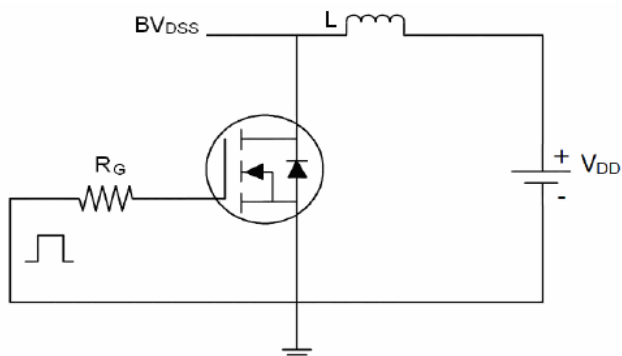
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V			±100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.8	1.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5 V, I <sub>D</sub> =20A		1.95	2.25	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =10A		2.05	2.6	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =30A	100			S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, F=1.0MHz		7870		PF
Output Capacitance	C <sub>oss</sub>			1510		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			1300		PF
SWITCHING CHARACTERISTICS (Note 4)						
Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω RL=0.5Ω		12.5		nS
Turn-on Rise Time	t <sub>r</sub>			35.5		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			40		nS
Turn-Off Fall Time	t <sub>f</sub>			32.5		nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =30A, V <sub>GS</sub> =4.5V		30.4		nC
Gate-Source Charge	Q <sub>gs</sub>			9.5		nC
Gate-Drain Charge	Q <sub>gd</sub>			19.8		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A			1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>				110	A
Reverse Recovery Time	trr	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 30A di/dt = 100A/us(Note3)		35.3		nS
Reverse Recovery Charge	Qrr			30.7		nC

## NOTES:

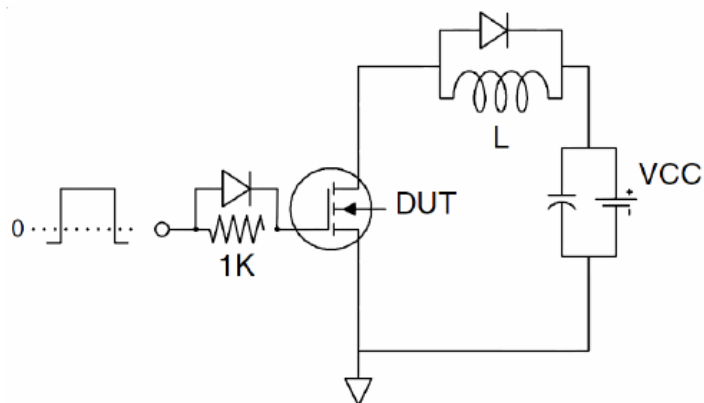
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in<sup>2</sup> FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing
5. EAS condation:  $T_J=25^\circ C, V_{dd}=20V, V_g=10V, L=0.5mH, R_g=25\Omega$

## Test circuit

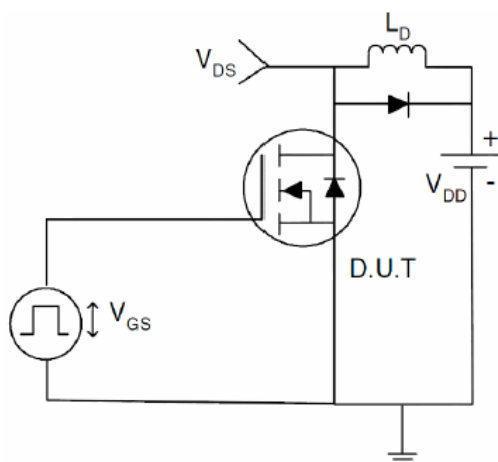
### 1) EAS Test Circuit



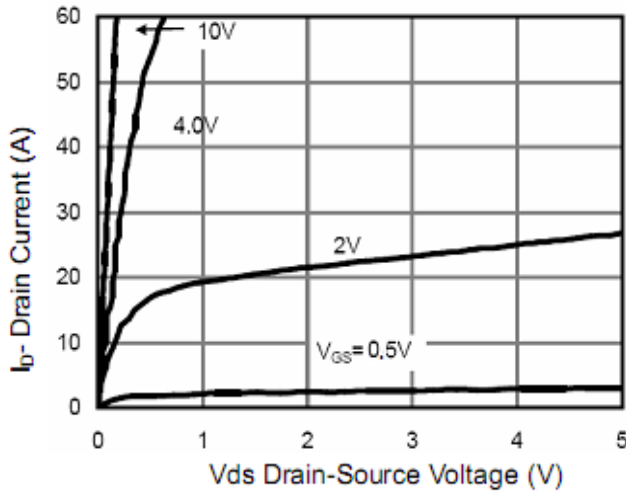
### 2) Gate Charge Test Circuit



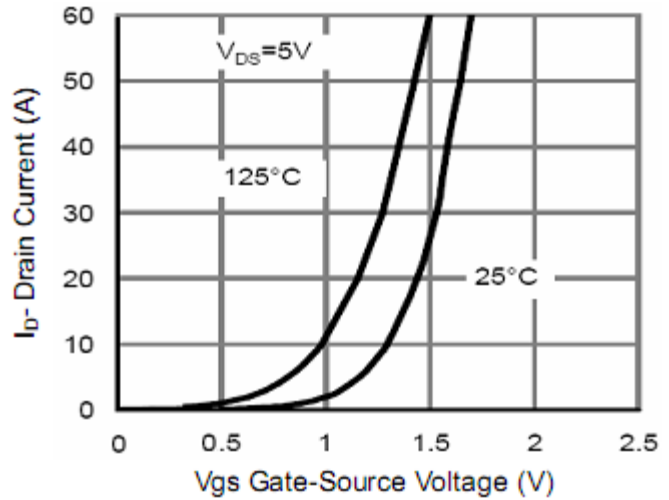
### 3) Switch Time Test Circuit



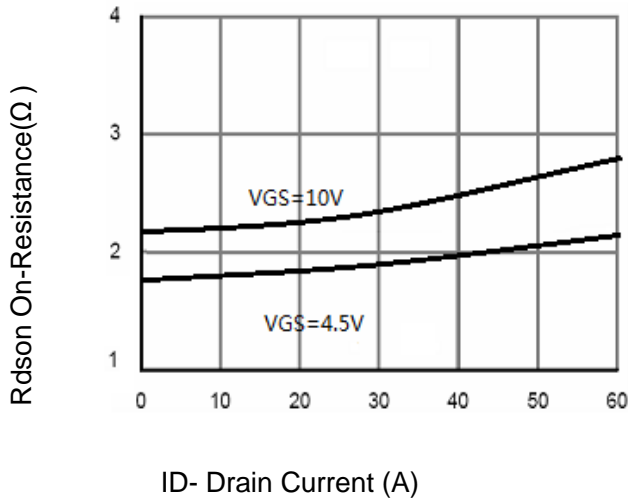
## Typical Electrical and Thermal Characteristics (Curves)



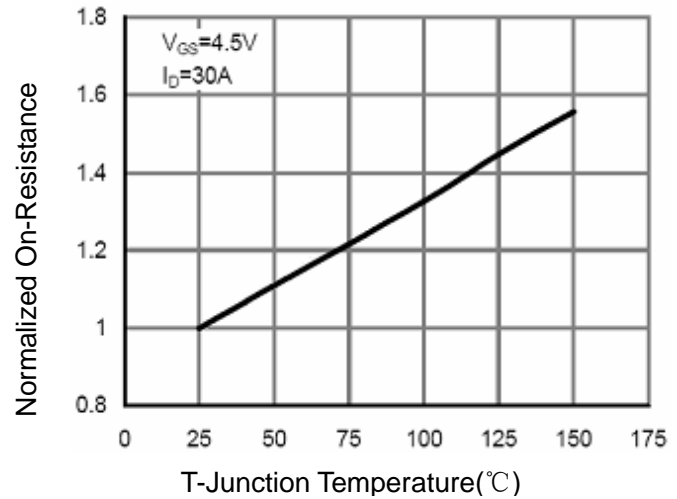
**Figure 1 Output Characteristics**



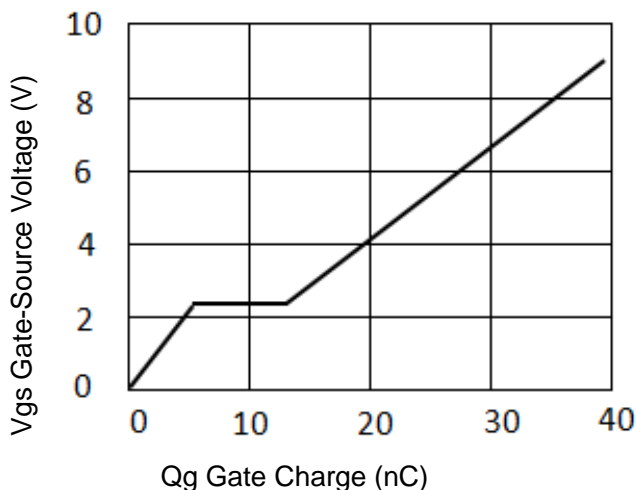
**Figure 2 Transfer Characteristics**



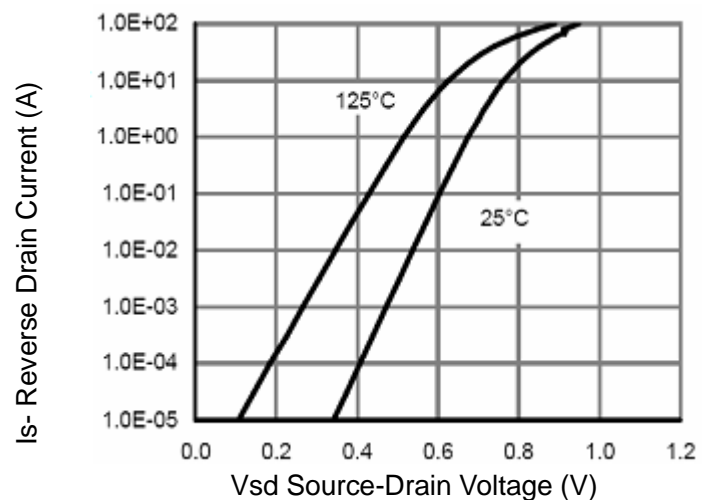
**Figure 3 Power Dissipation**



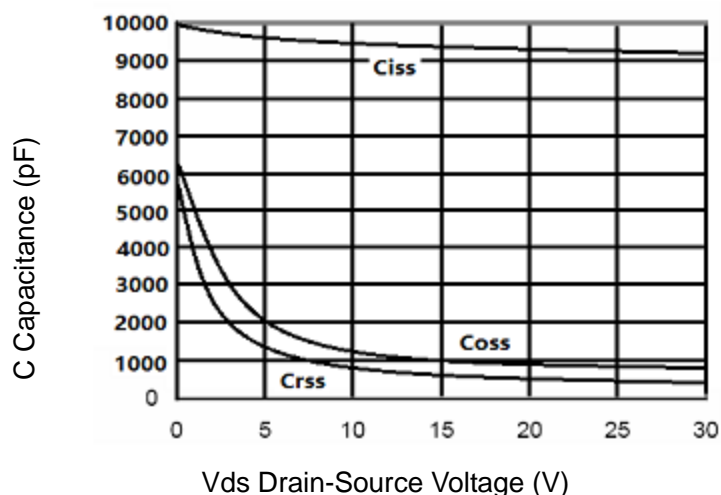
**Figure 4 RDS(on)-Junction Temperature**



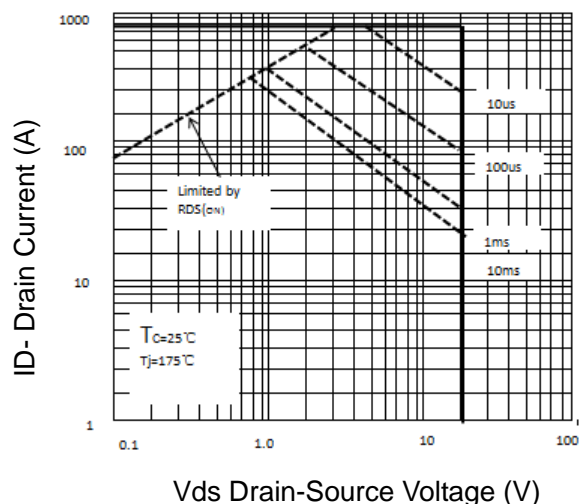
**Figure 5 Gate Charge**



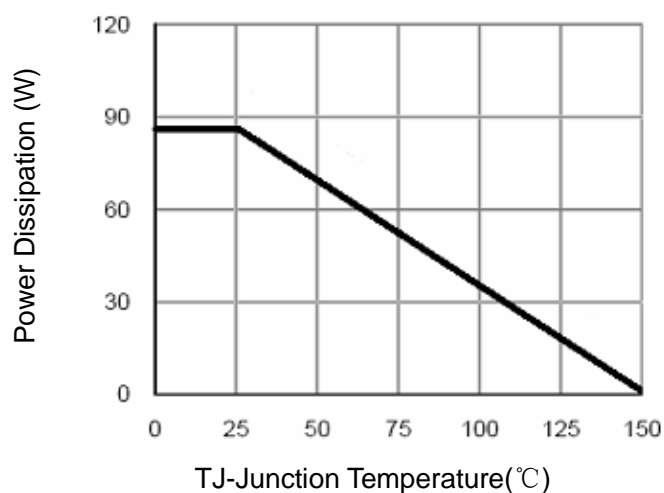
**Figure 6 Source- Drain Diode Forward**



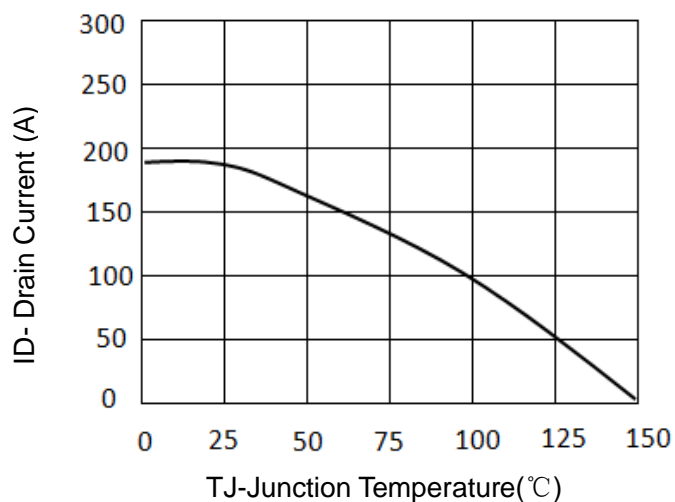
**Figure 7 Capacitance vs Vds**



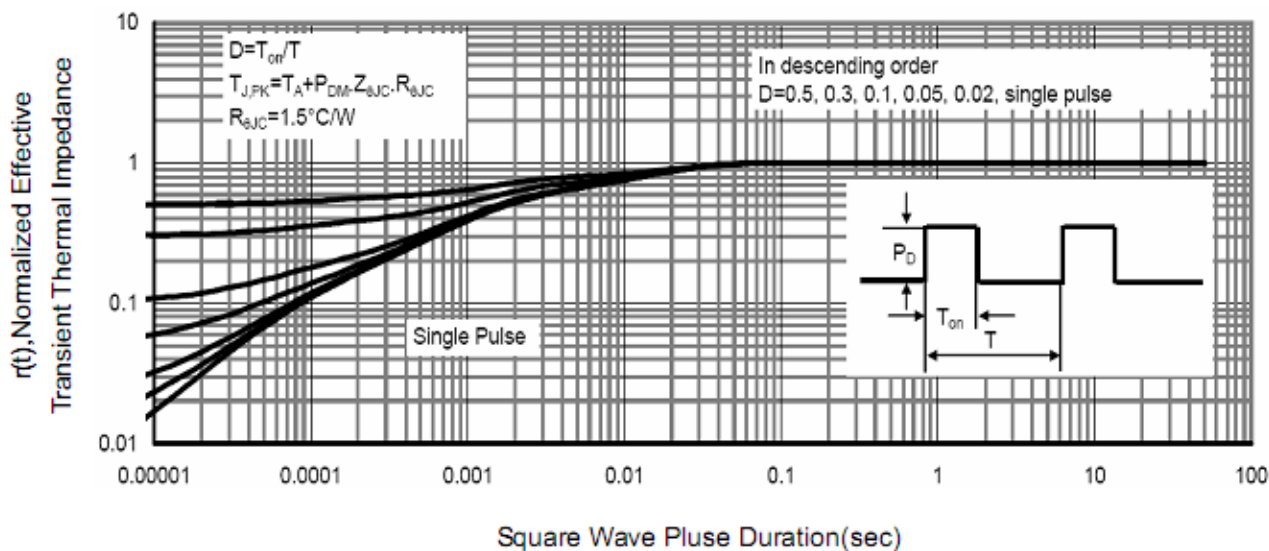
**Figure 8 Safe Operation Area**



**Figure 9 Power De-rating**

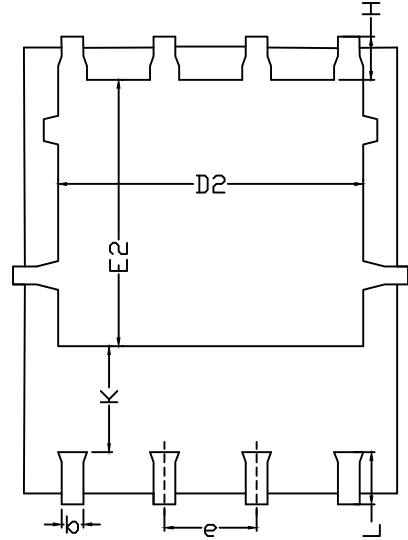
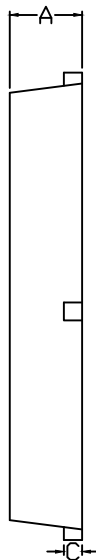
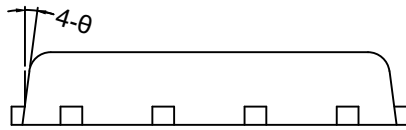
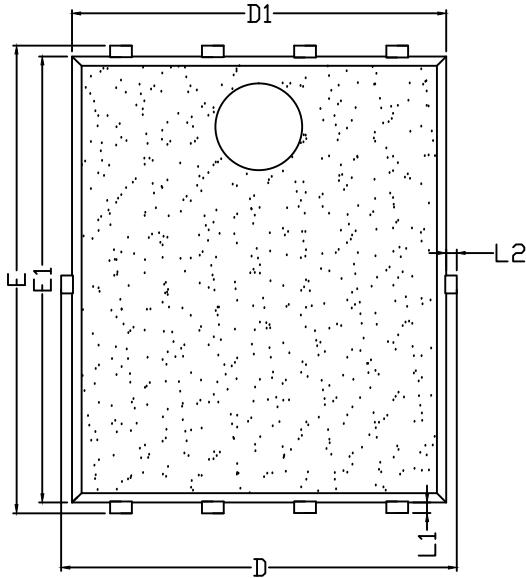


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN5X6 Package Information



SYMBOL	mm		
	MIN	NOM	MAX
*A	0.90	0.95	1.00
*b	0.25	0.30	0.35
*c	0.20	0.25	0.30
D	5.15BSC		
*D1	4.90	5.00	5.10
D2	3.90	4.05	4.20
*e	1.17	1.27	1.37
E	6.15BSC		
*E1	5.75	5.85	5.95
E2	3.35	3.50	3.65
H	0.51	0.61	0.71
K	1.10	—	—
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
L2	—	—	0.12
P	0.95	1.10	1.25
θ	9°	11°	13°

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